METHOD FOR FABRICATION OF A SEMICONDUCTOR STRUCTURE INCLUDING AN INTERPOSER FREE FROM ANY THROUGH VIA

ABSTRACT

The invention concerns a method of forming a semiconductor structure comprising: introducing, at selected conditions, hydrogen and helium species (e.g., ions) in a temporary support (1) to form a plane of weakness (2) at a predetermined depth therein, and to define a superficial layer (3) and a residual part (4) of the temporary support (1); forming on the temporary support (1) an interconnection layer (5); placing at least one semiconductor chip (6) on the interconnection layer (5); assembling a stiffener (8) on a backside of the at least one semiconductor chip (6); and providing thermal energy to the temporary support (1) to detach the residual part (4) and provide the semiconductor structure. The interconnection layer (5) forms an interposer free from any through via.

Fig. 7